

# 2SK2121

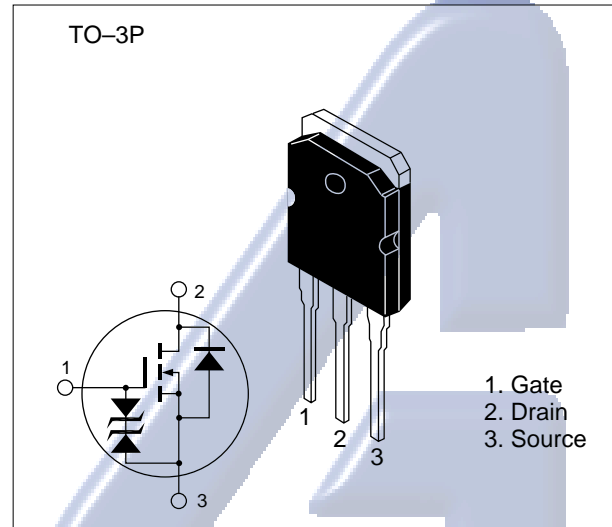
## Silicon N Channel MOS FET

### Application

High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for Switching regulator, DC – DC converter
- Avalanche ratings



**Table 1 Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	60	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	50	A
Drain peak current	I <sub>D(pulse)</sub> *	200	A
Body-drain diode reverse drain current	I <sub>DR</sub>	50	A
Avalanche current	I <sub>AP</sub> ***	50	A
Avalanche energy	E <sub>AR</sub> ***	214	mJ
Channel dissipation	P <sub>ch</sub> **	100	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 μs, duty cycle ≤ 1 %

\*\* Value at T<sub>c</sub> = 25 °C

\*\*\* Value at T<sub>ch</sub> = 25 °C, R<sub>g</sub> ≥ 50 Ω